

HERMETIC SILICON PHOTOTRANSISTOR

L14C1/C2

PACKAGE DIMENSIONS φD SEATING PLANE e φDI 3 Δ h U φ»-ή- []

ST1336

FEATURES

DESCRIPTION

wide angle, TO-18 package.

The L14C series is a silicon phototransistor mounted in a

- Hermetically sealed package
- Wide reception angle

SYMBOL	INC	HES	MILLIM	NOTES	
OTHEOL	MIN.	MAX.	MIN.	MAX.	10120
Α	_	210	—		
@b	.016	.021	.406	.534	
®D	.209	.230	5.30	5.85	
®D₁	.178 .195		4.52	4.96	
е	.100	NOM.	2.54	2	
e 1	.050	NOM.	1.27	2	
h		.030	—	.76	
j	.036	.046	.91	1.17	
k	.028	.048	.71	1.22	1
L	.500	_	12.7	_	
α	45°	45°	45°	45°	3

(COLLECTOR CONNECTED TO CASE) C (3) 8(2) E (I)

ST1605

NOTES:

- 1. MEASURED FROM MAXIMUM DIAMETER OF DEVICE.
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 LEADS HAVING MAXIMUM DIAMETER .021" (.533mm) MEASURED IN GAUGING PLANE .054" + .001" .000 (137 + 025 000mm) BELOW THE REFERENCE PLANE OF THE DEVICE SHALL BE WITHIN .007" (.778mm) THEIR TRUE POSITION RELATIVE TO MAXIMUM WIDTH TAB.
- 3. FROM CENTERLINE TAB.



SEMICONDUCTOR

HERMETIC SILICON PHOTOTRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C Unless Otherwise Specified))
Storage Temperature	−65°C to +150°C −65°C to +125°C
Soldering: Lead Temperature (Iron) Lead Temperature (Flow)	240°C for 5 sec. (3.4.5.6)
$\label{eq:constraint} \begin{array}{l} \mbox{Collector-Emitter Breakdown Voltage} & & & \\ \mbox{Collector-Base Breakdown Voltage} & & \\ \mbox{Emitter-Base Breakdown Voltage} & & \\ \mbox{Power Dissipation } (T_{A}=25^{\circ}\mbox{C}) & & \\ \mbox{Power Dissipation } (T_{c}=25^{\circ}\mbox{C}) & & \\ \mbox{Power Dissipation } (T_{c}=25^{\circ}\mbox{Power Dissipation } (T_{c}=25^{\circ}Po$	

ELECTRICAL CHARACTERISTICS (T ₄ = 25°C Unless Otherwise Specified) (All measurements made under pulse conditions.)									
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS			
Collector-Emitter Breakdown	BV _{CEO}	50		_	V	$I_{c} = 10 \text{ mA}, \text{ Ee} = 0$			
Emitter-Base Breakdown	BVEBO	7.0		_	V	$I_{\rm E} = 100 \mu A$, Ee = 0			
Collector-Base Breakdown	ВV _{сво}	50		_	V	$I_{c} = 100 \mu A, Ee = 0$			
Collector-Emitter Leakage	I _{CEO}	_		100	nA	$V_{ce} = 20 V, Ee = 0$			
Reception Angle at 1/2 Sensitivity	θ		±40		Degrees				
On-State Collector Current L14C1	I _{C(ON)}	1.0	· · ·		mA	Ee = 3.0 mW/cm ² , V _{CE} = 5 V ^(7,8)			
On-State Collector Current L14C2	C(ON)	0.5		_	mA	Ee = 3.0 mW/cm ² , V _{CE} = 5 V ^(7.8)			
On-State Collector Current L14C2	I _{C(ON)}	1.0			mA	Ee = 6.0 mW/cm ² , V _{CE} = 5 V ^(7,8)			
Turn-On Time	t _{on}		5		μS	$I_c = 2 \text{ mA}, V_{cc} = 10 \text{ V}, R_L = 100\Omega$			
Turn-Off Time	t _{off}	_	5	· · · · · ·	μS	$I_c = 2 \text{ mA}, V_{cc} = 10 \text{ V}, R_L = 100\Omega$			
Saturation Voltage	V _{CE(SAT)}			0.40	v	$l_c = 0.40 \text{ mA}, \text{ Ee} = 6.0 \text{ mW/cm}^{2(7.3)}$			

NOTES

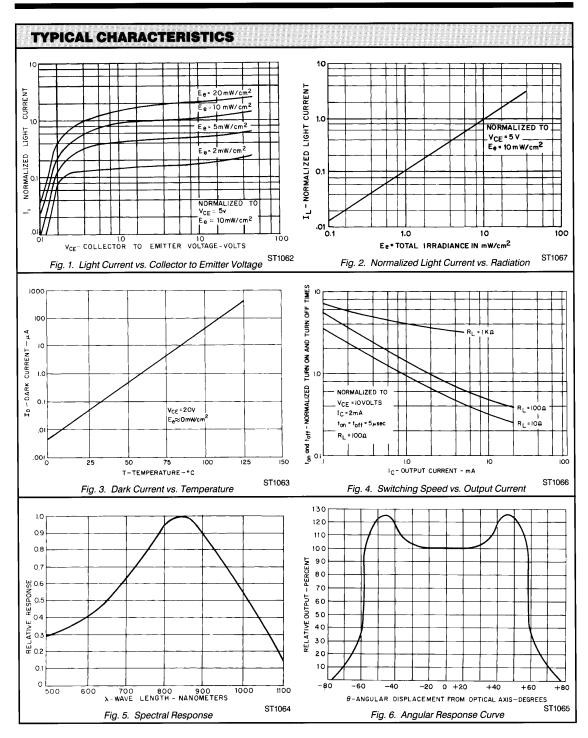
- 1. Derate power dissipation linearly 3.00mW/°C above 25°C ambient.

- Derate power dissipation linearly 5.00mW/°C above 25°C ambient.
 Derate power dissipation linearly 6.00mW/°C above 25°C case.
 RMA flux is recommended.
 Methanol or lsopropyl alcohols are recommended as cleaning agents.
 Soldering iron tip ¼e" (1.6 mm) minimum from housing.

- As long as leads are not under any stress or spring tension.
 Light source is a GaAs LED emitting light at a peak wavelength of 940 nm.
 Figure 1 and figure 2 use light source of tungsten lamp at 2870°K color temperature. A GaAs source of 3.0 mW/cm² is approximately equivalent to a tungsten source, at 2870°K, of 10 mW/cm².



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